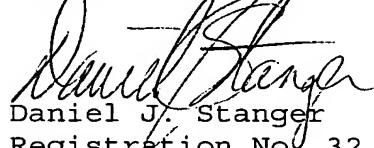


REMARKS

Claims 15-34 are now pending.

Respectfully submitted,


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ABSTRACT OF THE DISCLOSURE

A power amplifier system has a high frequency power amplifier circuit section employing source-grounded enhancement type n-channel MESFETs for receiving a drain bias voltage and a gate bias voltage of zero volts or positive low potentials supplied from a unipolar power supply, and amplifying a superposed input signal therewith to output an amplified signal indicative of a change in drain currents. An output matching circuit section applies impedance matching to the amplified signal and outputs the resultant signal. A gate bias voltage circuit section supplies a gate bias voltage to the high frequency power amplifier circuit. When a forward direct current gate voltage is applied to a gate terminal with a source terminal coupled to ground, the DC gate voltage becomes greater than or equal to 0.65 volts, the DC gate voltage causing a gate current value per gate width of 100 micrometers to exceed 100 microamperes.